



**ZXTN25040DFH**

**40V NPN MEDIUM POWER PLANAR TRANSISTOR IN SOT23**

**Features and Benefits**

- $BV_{CE0} > 40V$
- $I_C = 4A$  Continuous Collector Current
- Low Saturation Voltage  $V_{CE(sat)} < 55mV @ 1A$
- $R_{CE(sat)} = 35m\Omega$
- $h_{FE}$  characterised up to 10A
- High  $h_{FE}$  min 300 @ 1A
- 1.25W power dissipation
- 130V forward blocking voltage
- 6V reverse blocking voltage
- Complementary part number ZXTP25040DFH
- **“Lead-Free”, RoHS Compliant (Note 1)**
- **Halogen and Antimony Free. “Green” Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

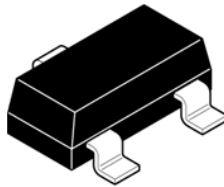
**Mechanical Data**

- Case: SOT23
- Case material: Molded Plastic. “Green” Molding Compound (Note 2) UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish; Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (Approximate)

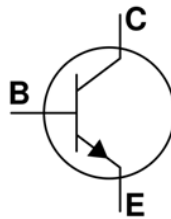
**Applications**

- MOSFET gate drivers
- Power switches
- Motor control
- DC fans
- DC-DC converters

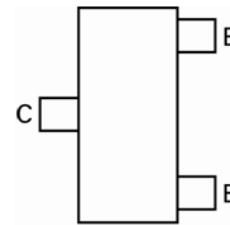
SOT23



Top View



Device Symbol



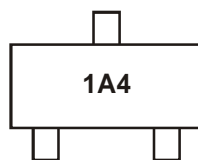
Top View  
Pin Configuration

**Ordering Information** (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN25040DFHTA	1A4	7	8	3,000

- Notes:
1. No purposefully added lead.
  2. Diodes Inc's “Green” Policy can be found on our website at <https://www.diodes.com/>
  3. Devices with lot number starting from PID0155145 (March 2010) are “Green” products.

**Marking Information**



1A4 = Product Type Marking Code

**Maximum Ratings** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

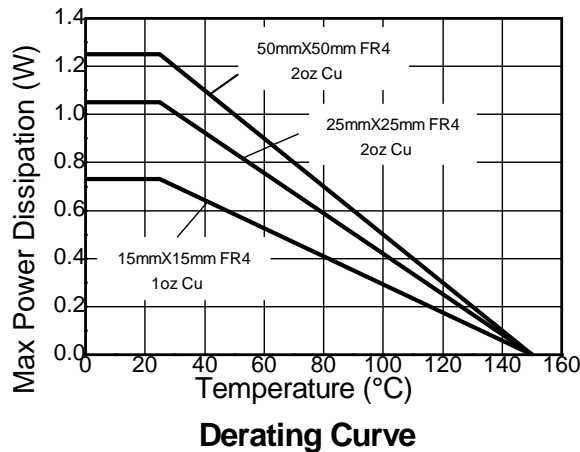
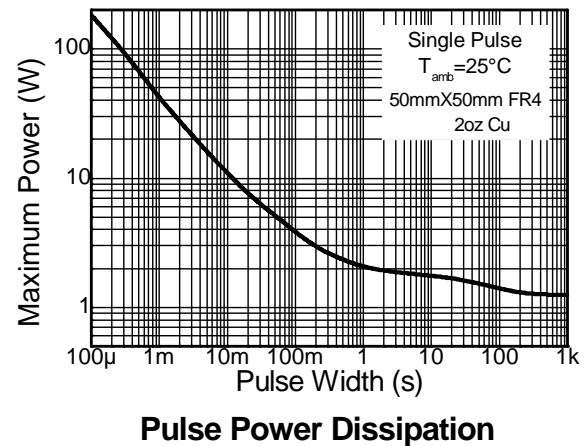
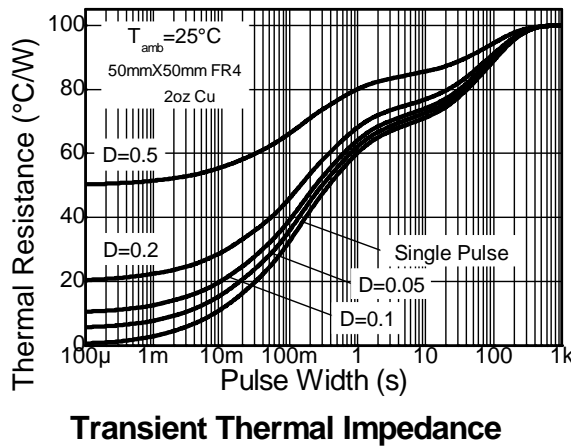
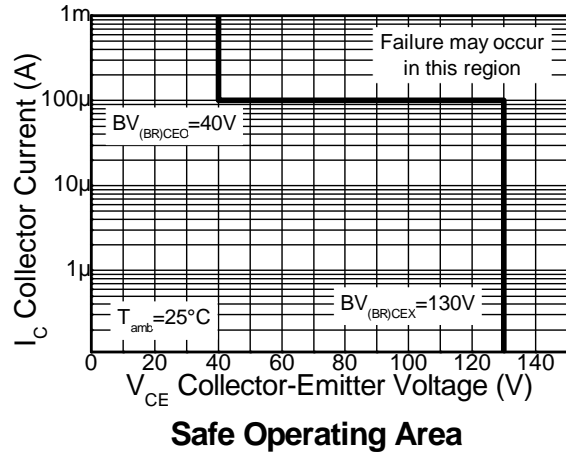
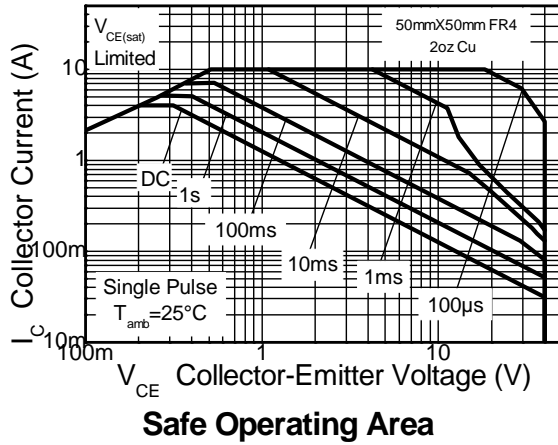
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	130	V
Collector-Emitter Voltage (Forward Blocking)	$V_{CEX}$	130	V
Collector-Emitter Voltage	$V_{CEO}$	40	V
Emitter-Collector Voltage (Reverse Blocking)	$V_{ECO}$	6	V
Emitter-Base Voltage	$V_{EBO}$	7	V
Continuous Collector Current (Note 6)	$I_C$	4	A
Peak Pulse Current	$I_{CM}$	10	A
Base Current	$I_B$	1	A

**Thermal Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor	$P_D$ -	0.73	W mW/°C
		5.84	
		1.05	
		8.4	
		1.25	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	9.6	°C/W
		1.81	
		14.5	
		171	
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	119	°C/W
		100	
		69	
		74.95	
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	°C

- Notes:
4. For a device surface mounted on 15mm X 15mm X 1.6mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  5. For a device surface mounted on 25mm X 25mm X 1.6mm FR4 PCB with high coverage of single sided 2 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  6. For a device surface mounted on 50mm X 50mm X 1.6mm FR4 PCB with high coverage of single sided 2 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  7. As note 6 above, measured at  $t < 5$  seconds
  8. Thermal resistance from junction to solder-point (at the end of the collector lead).

**Typical Thermal Characteristics**

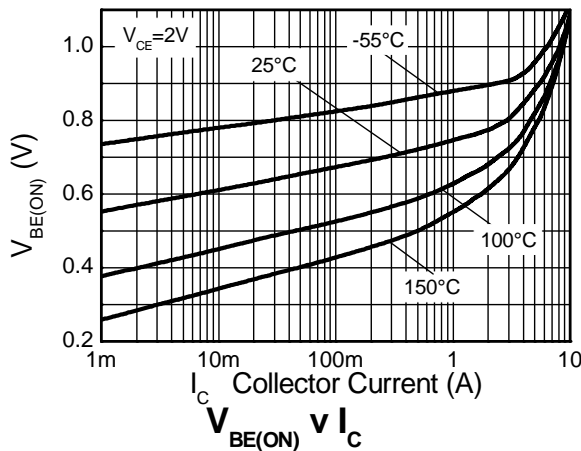
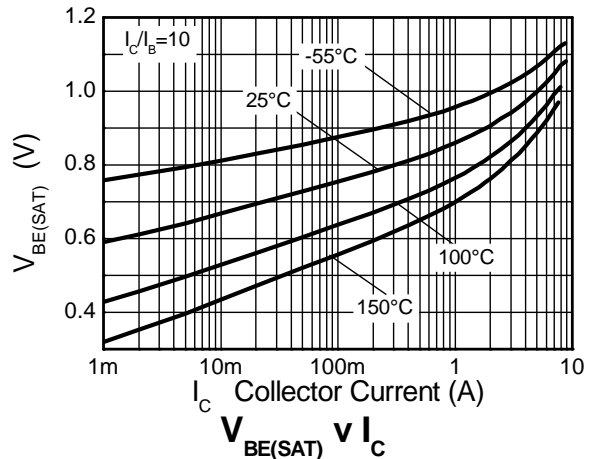
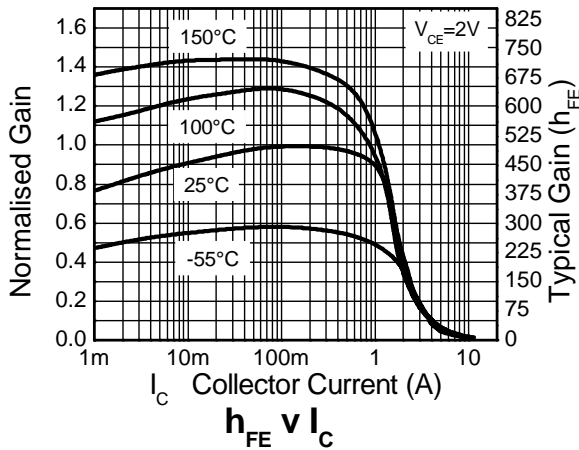
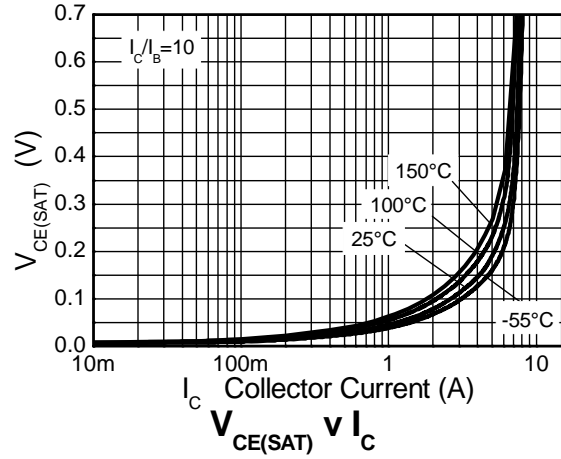
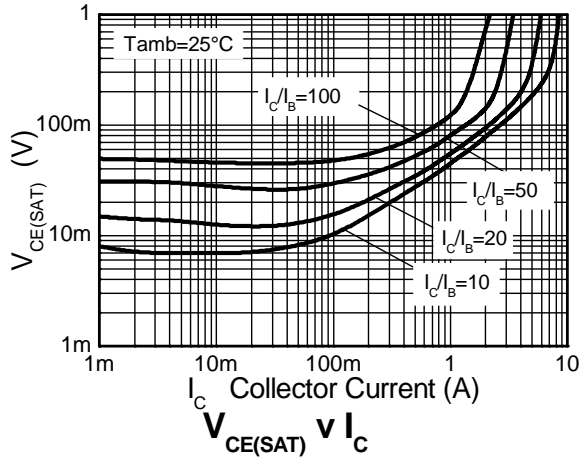


**Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

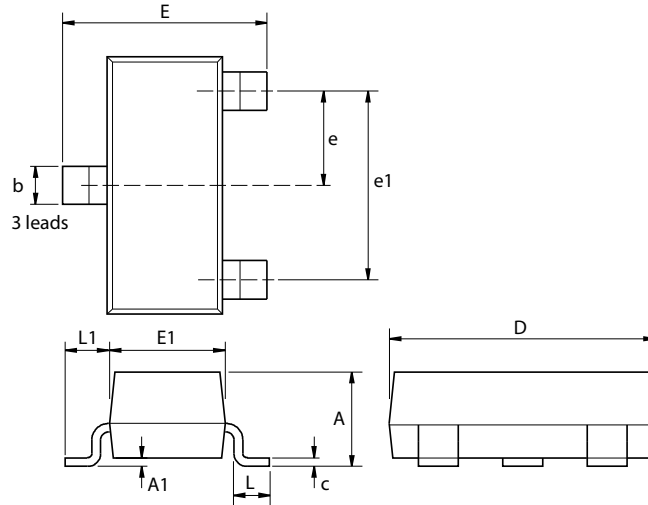
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Collector-Base Breakdown Voltage	BV <sub>CB0</sub>	130	170	-	V	I <sub>C</sub> = 100μA
Collector-emitter breakdown voltage (forward blocking)	BV <sub>CEX</sub>	130	170	-	V	I <sub>C</sub> = 100μA; R <sub>BE</sub> < 1kΩ or -1V < V <sub>BE</sub> < 0.25V
Collector-Emitter Breakdown Voltage (base open) (Note 9)	BV <sub>CEO</sub>	40	63	-	V	I <sub>C</sub> = 10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	8.3	-	V	I <sub>E</sub> = 100μA
Emitter-collector breakdown voltage (reverse blocking)	BV <sub>ECX</sub>	6	7.4	-	V	I <sub>E</sub> = 100μA; R <sub>BC</sub> < 1kΩ or -0.25V < V <sub>BC</sub> < 0.25V
Emitter-collector breakdown voltage (base open)	BV <sub>ECO</sub>	6	7.4	-	V	I <sub>E</sub> = 100μA;
Collector-base Cut-off Current	I <sub>CB0</sub>	-	<1	50	nA	V <sub>CB</sub> = 100V
				20	μA	V <sub>CB</sub> = 100V, T <sub>A</sub> = 100°C
Collector-emitter Cut-off Current	I <sub>CEX</sub>	-	-	100	nA	V <sub>CE</sub> = 100V; R <sub>BE</sub> < 1kΩ or -1V < V <sub>BE</sub> < 0.25V
Emitter-base Cut-off Current	I <sub>EBO</sub>	-	<1	50	nA	V <sub>EB</sub> = 5.6V
<b>ON CHARACTERISTICS (Note 9)</b>						
Static Forward Current Transfer Ratio	h <sub>FE</sub>	300	450	900	-	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 2V
		300	450	-		
		30	60	-		
		-	10	-		
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	-	45	55	mV	I <sub>C</sub> = 1A, I <sub>B</sub> = 100mA
		-	120	210		
		-	135	210		
		-	140	190		
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	-	960	1050	mV	I <sub>C</sub> = 4A, I <sub>B</sub> = 400mA
Base-Emitter On Voltage	V <sub>BE(on)</sub>	-	840	950	mV	I <sub>C</sub> = 4A, V <sub>CE</sub> = 2V
<b>SMALL SIGNAL CHARACTERISTICS (Note 9)</b>						
Transition Frequency	f <sub>T</sub>	-	190	-	MHz	I <sub>C</sub> = 50mA, V <sub>CE</sub> = 10V, f = 100MHz
Collector Output Capacitance	C <sub>obo</sub>	-	11.7	20	pF	V <sub>CB</sub> = 10V, f = 1MHz
Delay time	t <sub>d</sub>	-	64	-	ns	V <sub>CC</sub> = 10V, I <sub>C</sub> = 1A, I <sub>B1</sub> = I <sub>B2</sub> = 10mA
Rise time	t <sub>r</sub>	-	108	-	ns	
Storage time	t <sub>s</sub>	-	428	-	ns	
Fall time	t <sub>f</sub>	-	130	-	ns	

Notes: 9. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%

**Typical Electrical Characteristics**



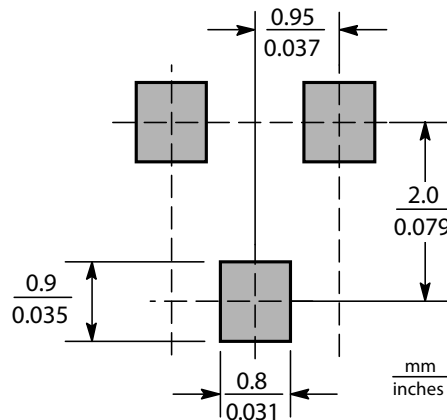
**Package Outline Dimensions**



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	-	1.12	-	0.044	e1	1.90 NOM		0.075 NOM	
A1	0.01	0.10	0.0004	0.004	E	2.10	2.64	0.083	0.104
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055
c	0.085	0.20	0.003	0.008	L	0.25	0.60	0.0098	0.0236
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024
e	0.95 NOM		0.037 NOM		-	-	-	-	-

**Note:** Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

**Suggested Pad Layout**



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